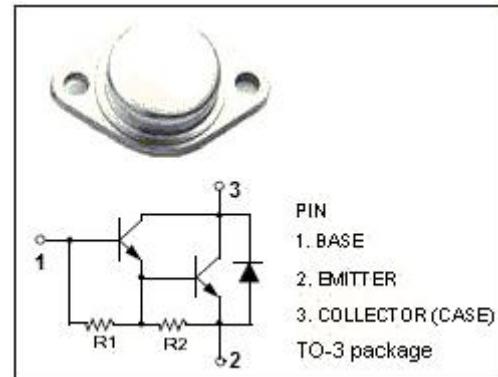


**DESCRIPTION**

- Built-in Base-Emitter Shunt Resistors
- High DC current gain-  
 $h_{FE} = 750$  (Min) @  $I_C = 10$  A
- Collector-Emitter Sustaining Voltage-  
 $V_{CEO(SUS)} = 100V$ (Min)
- Complement to type 2N6287

**APPLICATIONS**

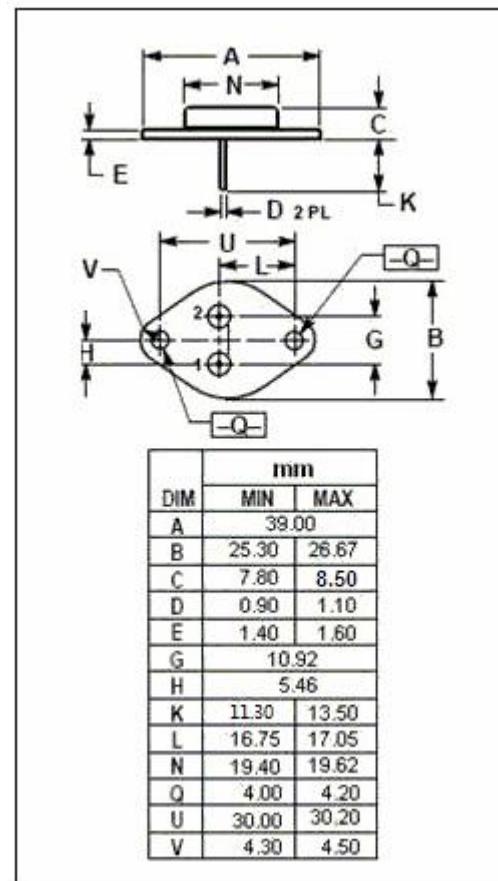
- Intended for general purpose amplifier and low frequency switching applications, such as linear and switching industrial equipment.

**ABSOLUTE MAXIMUM RATINGS( $T_c=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	100	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_C$	Collector Current -Continuous	20	A
$I_{CP}$	Collector Current-Peak	40	A
$I_B$	Base Current	0.5	A
$P_c$	Collector Power Dissipation@ $T_c=25^\circ C$	160	W
$T_j$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-65~150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	ThermalResistance, Junction to Case	1.09	°C/W



# SPTECH Product Specification

## SPTECH Silicon NPN Darlington Power Transistor

2N6284

### ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(sus)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	100		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 40mA		2.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 20A; I <sub>B</sub> = 200mA		3.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation voltage	I <sub>C</sub> = 20A; I <sub>B</sub> = 200mA		4.0	V
V <sub>BE(on)</sub>	Base-Emitter On voltage	I <sub>C</sub> = 10A ; V <sub>CE</sub> = 3V		2.8	V
I <sub>CEO</sub>	Collector Cutoff current	V <sub>CE</sub> = 50V; I <sub>B</sub> =0		1.0	mA
I <sub>CEx</sub>	Collector Cutoff current	V <sub>CE</sub> = 100V; V <sub>BE(off)</sub> = 1.5V V <sub>CE</sub> = 100V; V <sub>BE(off)</sub> = 1.5V, T <sub>c</sub> =150°C		0.5 5.0	mA
I <sub>EBO</sub>	Emitter Cut-off current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		2.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 10A ; V <sub>CE</sub> = 3V	750	18000	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 20A ; V <sub>CE</sub> = 3V	100		
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		400	pF

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